6000–18000 MHz GaN MMIC Power Amplifier Die

LCI-PA-6000-18000-PS45T is a GaN MMIC power amplifier supplied as bare die for 6000–18000 MHz. It supports CW and pulsed operation.

The RF table specifies: Saturated output power: 45 dBm (typical); Power gain: 20 dB (typical); Power-added efficiency: 23 % (typical). RF test conditions: TA = +25 °C; Vd = +28 V; Vg = -2.2 V. Die dimensions: 4.52 × 5.82 × 0.1 mm.



RF characteristics

TA = +25 °C; Vd = +28 V; Vg = -2.2 V

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Operating frequency	f	6000	-	18000	MHz
Saturated output power	Psat	44.5	45	-	dBm
Power gain	Gp	19.5	20	-	dB
Power-gain flatness	ΔGp	-	-	±1	dB
Power-added efficiency	PAE	-	23	-	%
Small-signal gain	S21	-	30	-	dB
Small-signal gain flatness	ΔS21	-	-	±3	dB
Input VSWR	VSWR(in)	-	1.6	3	-

DC bias and current

TA = +25 °C

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Drain voltage	Vd	-	28	32	V
Gate voltage	Vg	-3	-2.2	-2	V
Quiescent drain current	Id	-	4.4	-	A
Dynamic drain current	Idd	-	6	7	A
Dynamic gate current	Igg	-	3	10	mA

Absolute limits

Absolute limits; these are not normal operating targets.

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Maximum drain-source voltage	Vd	-	-	32	V
Minimum gate bias	Vg	-5	-	-	V
Maximum input power	Pin	-	-	30	dBm
Maximum channel temperature	Top	-	-	225	°C
Storage temperature	TSTG	-65	-	150	°C

Die dimensions

Parameter	Value	Unit
Die dimensions	4.52 × 5.82 × 0.1	mm
Plan-view outline tolerance	±100 (Plan-view outline only; the source does not specify thickness tolerance.)	µm

Current publication record · 1.7 · 2026-11-12. Product description or editorial content updated. Replaces revision 1.6.

Die integration and bias sequencing

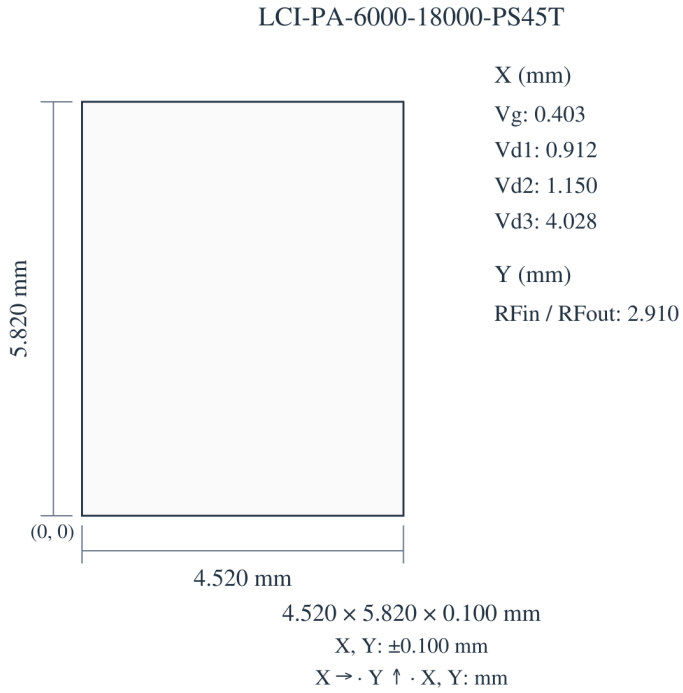
Apply gate bias before drain bias at power-up. At power-down, remove drain bias before gate bias. Use clean handling, ESD protection and a carrier with thermal expansion compatible with the SiC die.

Bond-pad dimensions

Symbol: RFin; Dimensions (µm): 100 × 100. Symbol: Vg; Dimensions (µm): 130 × 100. Symbol: Vd1; Dimensions (µm): 130 × 100. Symbol: Vd2; Dimensions (µm): 120 × 100. Symbol: Vd3; Dimensions (µm): 250 × 150. Symbol: RFout; Dimensions (µm): 150 × 150.

Mechanical Outline

Outline and dimensioned coordinates in mm. Use this drawing as a dimensional reference. Fabrication and wire bonding require complete drawings.

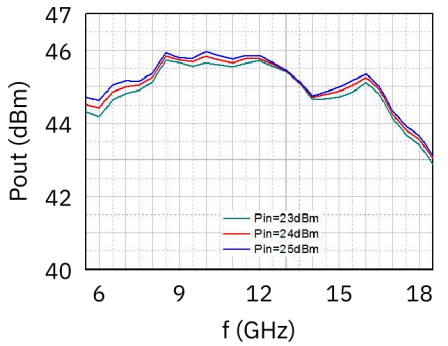


Performance curves

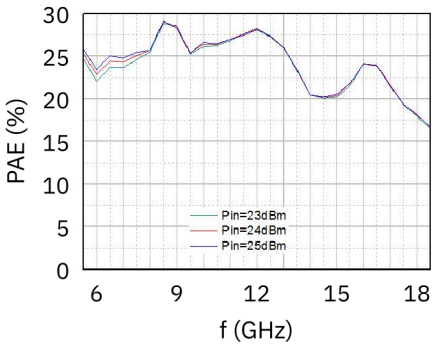
Each performance plot applies to its stated operating conditions.

Pulsed — Output power; Power-added efficiency; Drain current; Small-signal gain; Input matching.

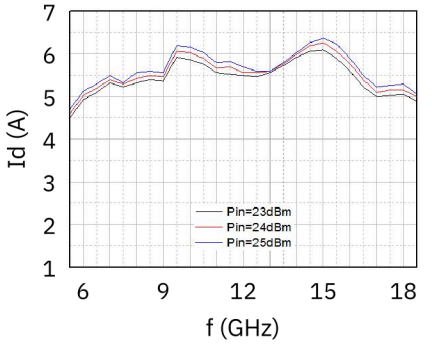
Figure notes: Vd=+24V; Vg=-2.2V. D = 10%; (1–3): Pin = 23 / 24 / 25 dBm. Conditions apply to the indicated plots and their own legends.



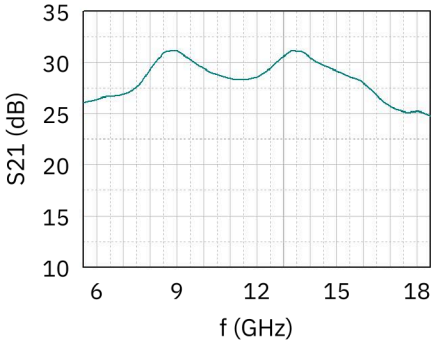
Pin = 23 dBm Pin = 25 dBm
Pin = 24 dBm

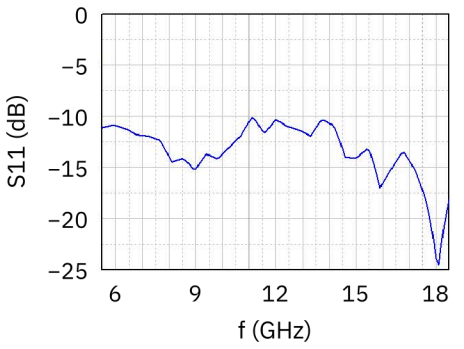


Pin = 23 dBm Pin = 25 dBm
Pin = 24 dBm



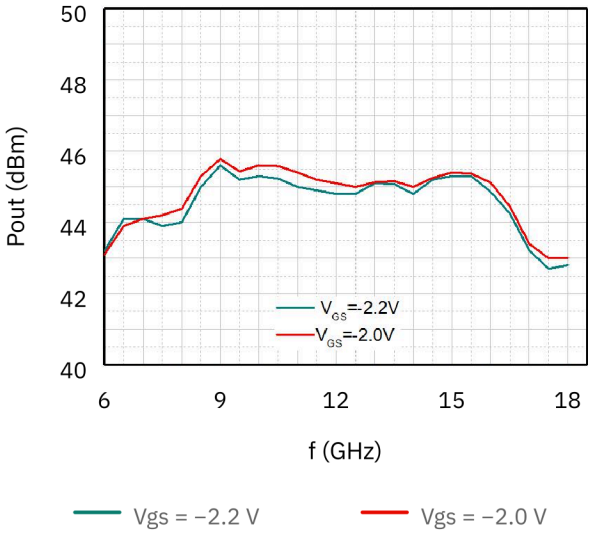
Pin = 23 dBm Pin = 25 dBm
Pin = 24 dBm

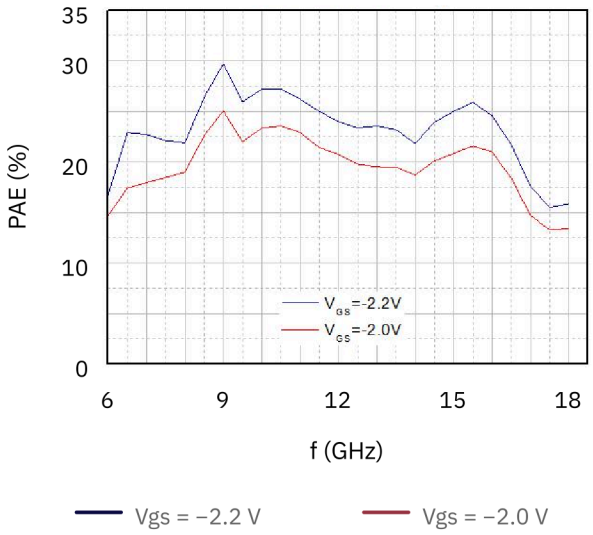


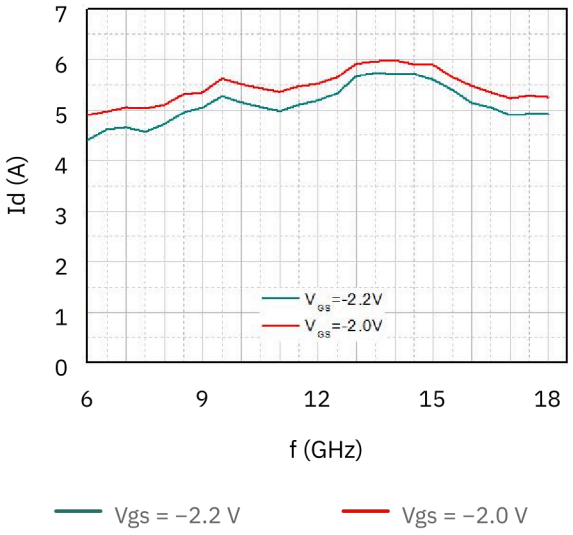


Continuous wave (CW) — Output power; Power-added efficiency; Drain current.

Figure notes: Vd=+28V; Pin=25dBm.









Document notice

Specifications are subject to revision. Before design release, confirm the current document revision and product-specific requirements with LCRF. The approved quotation and order documentation define the supplied configuration.